

## **METHOD FOR FABRICATING A SEMICONDUCTOR DEVICE**

### **ABSTRACT OF THE DISCLOSURE**

A method for fabricating a semiconductor device, including forming a gate insulating film and a gate electrode film on a semiconductor substrate, and patterning the gate electrode film to form a gate electrode. A portion of the gate insulating film is removed to form an undercut region beneath the gate electrode. A buffer silicon film is formed over an entire surface of the resultant substrate to cover the gate electrode and to fill the undercut region. The buffer silicon film is selectively oxidized to form a buffer silicon oxide film.